

BUK6C3R3-75C

N-channel TrenchMOS intermediate level FET

Rev. 3 — 18 January 2012

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in high-performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- High current handling capability, up to 320 A
- Low conduction losses due to very low on-state resistance
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoids
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	75	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	-	181	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	300	W
Static chara	cteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 90 A; T_j = 25 °C; see <u>Figure 11</u>	-	2.85	3.4	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cha	racteristics					
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	76	-	nC
Avalanche ru	ıggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A; } V_{sup} < 75 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	560	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	mb	D
3	S	source		
4	D	drain[1]	1	
5	S	source	——————————————————————————————————————	mbb076 S
6	S	source	123 567	
7	S	source	SOT427 (D2PAK)	
mb	D	mounting base; connected to drain		

^[1] It is not possible to connect to pin 4 of the SOT427 package.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6C3R3-75C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 7 leads (one lead cropped)	SOT427

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		9 , (
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V_{GS}	gate-source voltage	Pulsed	<u>[1]</u> -20	20	V
		DC	<u>[2]</u> -16	16	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	181	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	-	128	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see <u>Figure 3</u>	-	723	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	300	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
Is	source current	T _{mb} = 25 °C	-	181	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	723	Α
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 120 A; V_{sup} < 75 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	560	mJ

- [1] Accumulated pulse duration not to exceed 5mins.
- [2] -16V accumulated duration not to exceed 168 hrs.

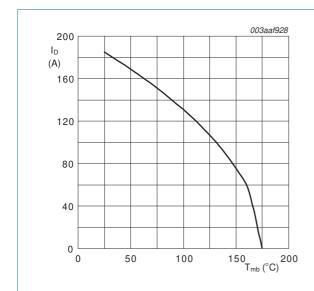


Fig 1. Continuous drain current as a function of mounting base temperature

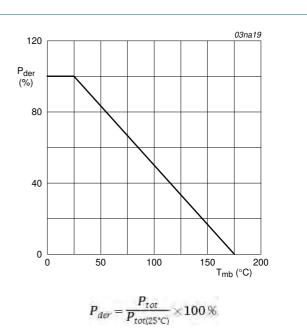
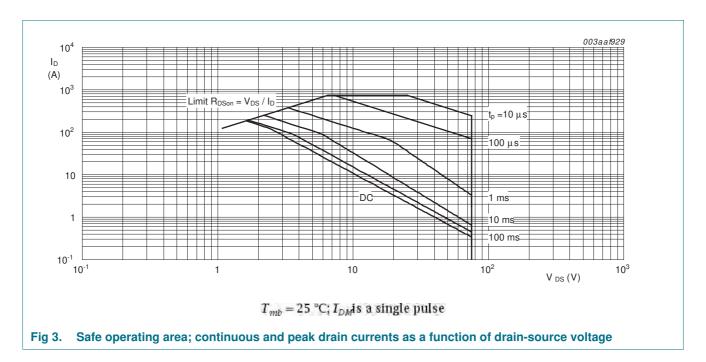


Fig 2. Normalized total power dissipation as a function of mounting base temperature

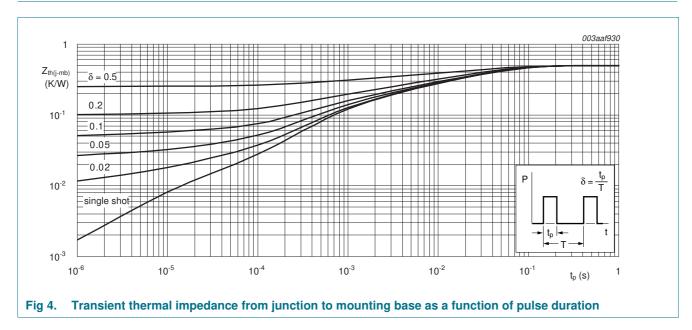
BUK6C3R3-75C



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	75	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	68	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
V _{GSth} gate-sour voltage	gate-source threshold voltage	I_D = 2.5 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 10</u>	8.0	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	3.3	V
I _{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.04	1	μΑ
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 90 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	2.85	3.4	mΩ	
		$V_{GS} = 5 \text{ V}; I_D = 90 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u>	-	3.35	4.3	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 90 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	3.7	5.1	mΩ	
		V_{GS} 10 V; I_D = 90 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	9.2	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	253	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; $V_{GS} = 5 \text{ V}$; see Figure 13; see Figure 14	-	140	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V};$	-	45	-	nC
Q_{GD}	gate-drain charge	see Figure 13; see Figure 14	-	76	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	11840	15800	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	873	1050	pF
C _{rss}	reverse transfer capacitance		-	546	750	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.4 \Omega; V_{GS} = 10 \text{ V};$	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	217	-	ns
t _{d(off)}	turn-off delay time		-	384	-	ns
t _f	fall time		-	165	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 80 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	63	-	ns
Qr	recovered charge	$V_{DS} = 40 \text{ V}$	-	165	-	nC

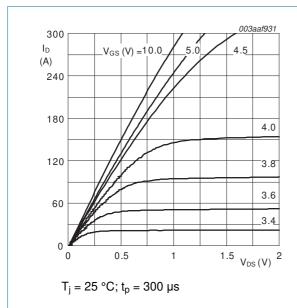


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

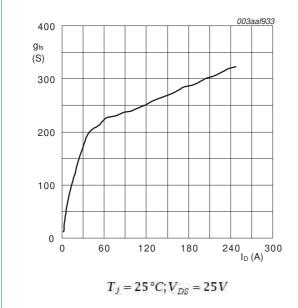


Fig 7. Forward transconductance as a function of drain current; typical values

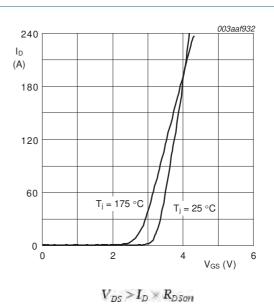
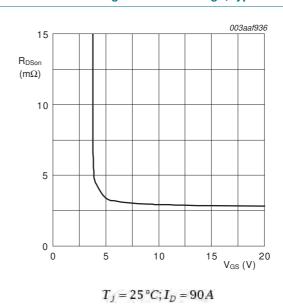


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



ig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

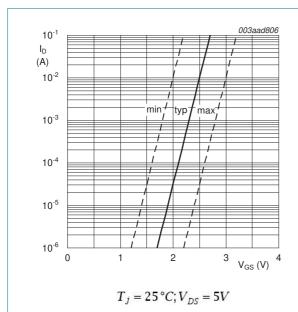


Fig 9. Sub-threshold drain current as a function of gate-source voltage

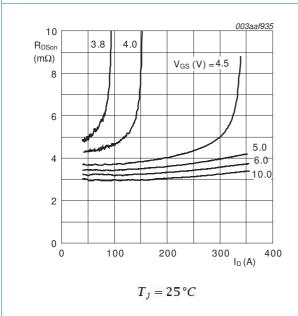


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

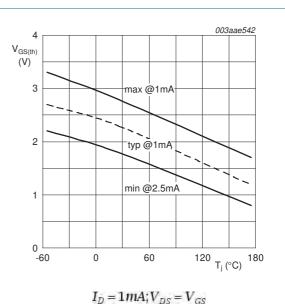


Fig 10. Gate-source threshold voltage as a function of junction temperature

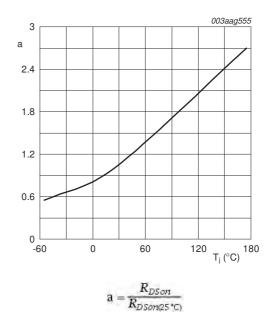
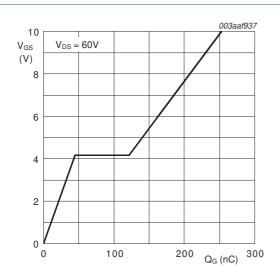


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j = 25 \, ^{\circ}C; \, I_D = 25 \, A$

Fig 13. Gate-source voltage as a function of gate charge; typical values

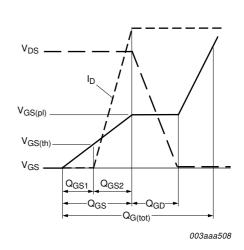
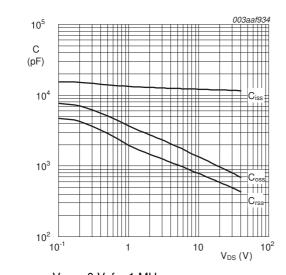
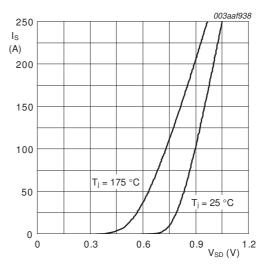


Fig 14. Gate charge waveform definitions



 $V_{GS} = 0 V; f = 1 MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0 V$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

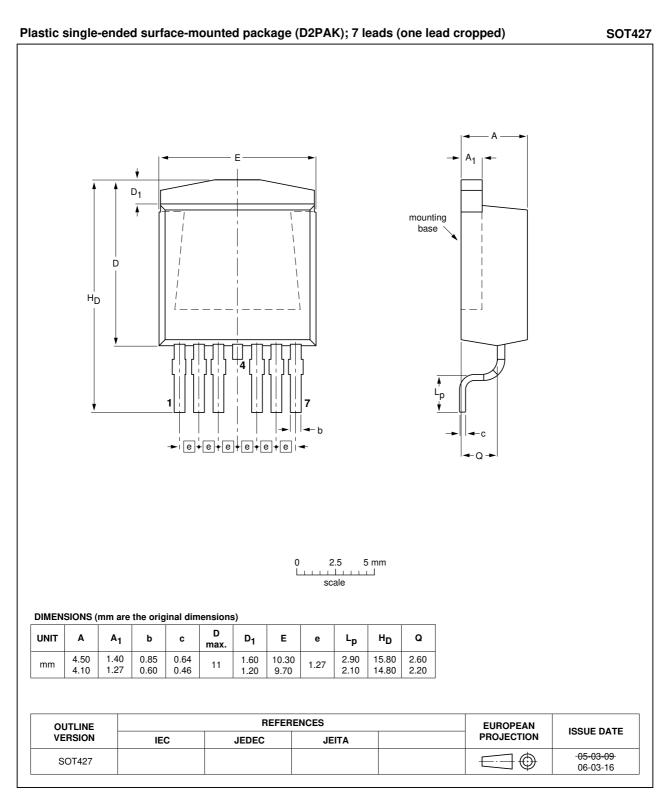


Fig 17. Package outline SOT427 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6C3R3-75C v.3	20120118	Product data sheet	-	BUK6C3R3-75C v.2
Modifications:	 Status char 	ged from preliminary to product.		
BUK6C3R3-75C v.2	20111221	Preliminary data sheet	-	BUK6C3R3-75C v.1

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Nexperia

BUK6C3R3-75C

N-channel TrenchMOS intermediate level FET

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